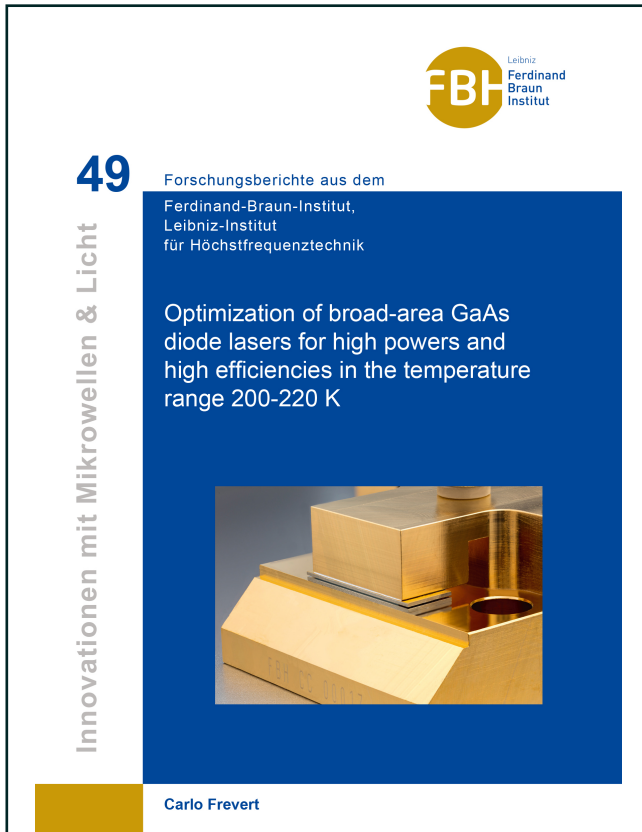




Carlo Frevert (Autor)

Optimization of broad-area GaAs diode lasers for high powers and high efficiencies in the temperature range 200-220 K



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Contents

1	Introduction	1
2	Theoretical background of high power, high efficiency diode lasers	7
2.1	Basic principles of AlGaAs / InGaAs based diode lasers	7
2.1.1	Lasing threshold	10
2.1.2	Optical output power	12
2.1.3	Electro-optical conversion efficiency	13
2.1.4	Waste heat	14
2.1.5	Influence of laser parameters on output power and efficiency	15
2.2	Semiconductor properties at reduced temperatures	19
2.2.1	Bulk conductivity at lower temperatures	20
3	Measurement Setup	23
3.1	Room temperature measurement setups	23
3.1.1	Electro-optical and spectral characterization	24
3.1.2	Histogram of diode laser bars	26
3.1.3	Low temperature prototype setup	27
3.2	Low temperature measurement setup: first generation	29
3.2.1	Physical setup of low temperature measurement station	29
3.2.2	Power calibration	31
3.3	Final Cryo-measurement setup	33
3.3.1	Changes to the physical setup	33
3.3.2	QCW power calibration by pulse shape analysis	33
4	Benchmark Designs (Iteration 0)	37
4.1	Performance of established vertical designs	37
4.1.1	High power room temperature optimized designs	38
4.1.2	Performance of thick waveguide Asloc configuration at decreasing temperature	39
4.1.3	Performance of Asloc configuration with changing waveguide composition at decreasing temperature	43
4.1.4	Performance of Edas configuration at decreasing temperature	46
4.1.5	Selection of benchmark designs	49
4.2	Low temperature performance of benchmark designs	50
4.2.1	Fabrication of high power, high efficiency single emitters and bars	50



4.2.2	Design1: Impact of lateral layout and length on performance	51
4.2.3	Design2: Performance up to high currents	57
4.3	Conclusions from Iteration 0	62
5	Low Al-content Structures (Iteration 1)	65
5.1	Design and Optimization of Low Resistance Structures	66
5.1.1	Options to reduce series resistance	66
5.1.2	Vertical design of low resistance structures	68
5.1.3	Short pulse measurements of designs with low Al-content in the waveguide	71
5.1.4	Low Temperature Length-Dependent Measurements	73
5.1.5	Measurement of Al-content Matrix	77
5.2	High power operation of low series resistance designs	84
5.2.1	Selection of promising designs	84
5.2.2	Fabrication of low operation temperature lasers	85
5.2.3	Characterization of single emitters	87
5.2.4	Characterization of bars	93
5.2.5	Estimation of loss mechanisms	103
5.3	Conclusions from Iteration 1	105
6	Low Al-content, thin waveguide designs (iteration 2)	107
6.1	Al-variation in thin waveguide designs	108
6.1.1	Vertical design of thin WG structures	108
6.1.2	Internal parameters at room temperature	111
6.1.3	Electrical properties and behavior at low temperatures	113
6.2	High power operation of bars and single emitters	117
6.2.1	Fabrication of high power bars and single emitters	117
6.2.2	Comparison of short loop and fully processed diodes	119
6.2.3	Temperature dependent performance of bars and single emitters . .	120
6.2.4	High power performance of bars with thin, asymmetric wave-guide designs	123
6.2.5	Estimation of loss mechanisms	128
6.3	Conclusions from iteration 2	130
7	Summary and Outlook	131
	Appendix	135
	List of figures	137
	List of tables	139
	Bibliography	140